

Silicon NPN Power Transistors**2SC3298 2SC3298A 2SC3298B****DESCRIPTION**

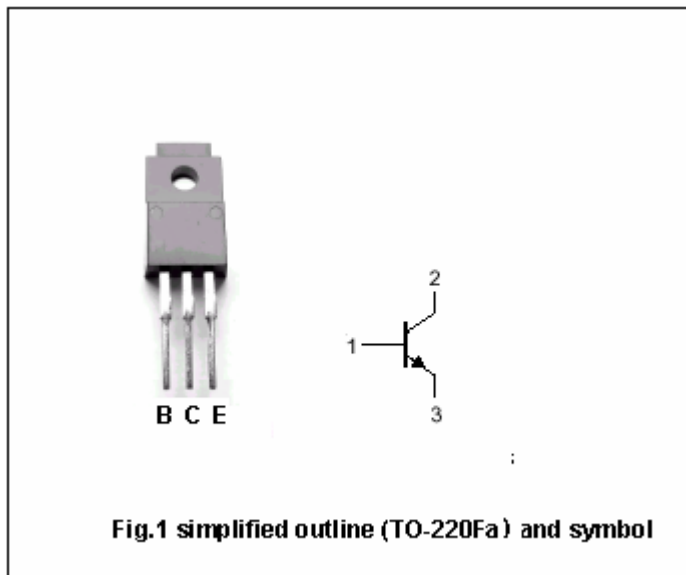
- With TO-220Fa package
- Complement to type
2SA1306,2SA1306A,2SA1306B

APPLICATIONS

- Power amplifier applications
- Driver stage amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

**Absolute maximum ratings (Ta=25℃)**

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SC3298	Open emitter	160	V
		2SC3298A		180	
		2SC3298B		200	
V_{CEO}	Collector-emitter voltage	2SC3298	Open base	160	V
		2SC3298A		180	
		2SC3298B		200	
V_{EBO}	Emitter-base voltage		Open collector	5	V
I_C	Collector current			1.5	A
I_B	Base current			0.15	A
P_C	Collector power dissipation		$T_C=25^{\circ}\text{C}$	20	W
T_j	Junction temperature			150	℃
T_{stg}	Storage temperature			-55~150	℃

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SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SC3298	$I_C=10mA, I_B=0$	160			V
		2SC3298A		180			
		2SC3298B		200			
V_{CEsat}	Collector-emitter saturation voltage		$I_C=0.5A, I_B=50mA$			1.5	V
V_{BE}	Base-emitter voltage		$I_C=0.5A, V_{CE}=5V$			1.0	V
I_{CBO}	Collector cut-off current		$V_{CB}=160V, I_E=0$			1.0	μA
I_{EBO}	Emitter cut-off current		$V_{EB}=5V, I_C=0$			1.0	μA
h_{FE}	DC current gain		$I_C=0.1A; V_{CE}=5V$	70		240	
C_{ob}	Output capacitance		$I_E=0; V_{CB}=10V, f=1MHz$		25		pF
f_T	Transition frequency		$I_C=0.1A; V_{CE}=10V$		100		MHz

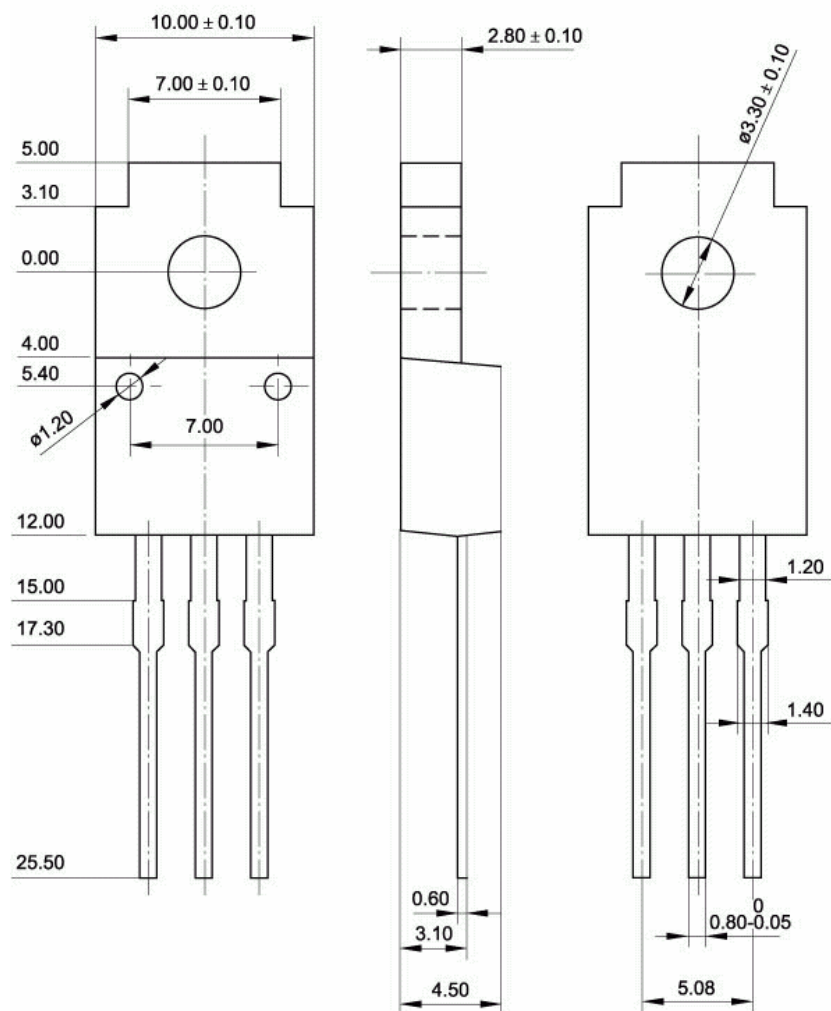
◆ h_{FE} Classifications

O	Y
70-140	120-240

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PACKAGE OUTLINE

Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)